TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (L^2 - π -MOSVI)

2SJ537

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain–source ON resistance : RDS (ON) = 0.16 Ω (typ.)

• High forward transfer admittance $: |Y_{fs}| = 3.5 \text{ S (typ.)}$ • Low leakage current $: I_{DSS} = -100 \,\mu\text{A (V}_{DS} = -50 \,\text{V)}$

• Enhancement-mode : $V_{th} = -0.8 \sim -2.0 \text{ V (V}_{DS} = -10 \text{ V, I}_{D} = -1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-50	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	-50	٧	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	-5	Α	
	Pulse (Note 1)	I _{DP}	-15	Α	
Drain power dissipation		P_{D}	0.9	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Thermal Characteristics

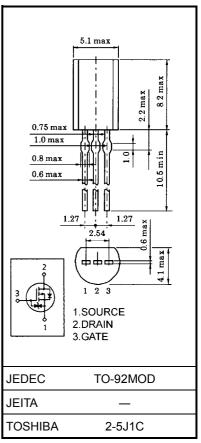
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch-a)}	138	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device.

Please handle with caution.

Unit: mm



Weight: 0.36 g (typ.)

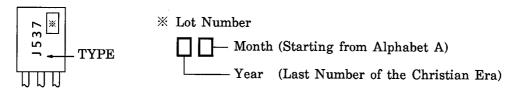
Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cut-off cur	rent	I _{DSS}	$V_{DS} = -50 \text{ V}, V_{GS} = 0 \text{ V}$	1	_	-100	μΑ
Drain-source brovoltage	eakdown	V _{(BR)DSS}	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	- 50	_	_	٧
Gate threshold v	oltage	V_{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	_	-2.0	V
Drain-source ON resistance		Pro (ON)	$V_{GS} = -4 \text{ V}, I_D = -1.3 \text{ A}$		0.27	0.34	Ω
		R _{DS} (ON)	$V_{GS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	_	0.16	0.19	12
Forward transfer	admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	1.5	3.5	_	S
Input capacitanc	е	C _{iss}		_	470	_	
Reverse transfer capacitance		C _{rss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	60	_	pF
Output capacitance		Coss			210	_	
Switching time	Rise time	t _r	V _{GS} -10V I _D =-2.5A V _{OUT} R _L =10Ω	_	25	_	ns
	Turn-on time	t _{on}		l	35	_	
	Fall time	t _f		_	20	_	
	Turn-off time	t _{off}	$V_{DD} = -25V$ Duty $\leq 1\%$, $t_{W} = 10 \mu s$	_	120	_	
Total gate charge (Gate-source plus gate-drain)		Qg	V _{DD} ≈ -40 V, V _{GS} = -10 V,	_	18		nC
Gate-source charge		Q _{gs}	I _D = -5 A	_	13	_	
Gate-drain ("miller") charge		Q_{gd}		_	5	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	-	_	_	-5	Α
Pulse drain reverse current (Note 1)	I _{DRP}		l	l	-15	Α
Forward voltage (diode)	V_{DSF}	$I_{DR} = -5 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.5	V

Marking



2 2002-09-04

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